



DCT-1603010102010200 Seat No. _____

M. Sc. (Sem. I) (CBCS) Examination

August - 2022

Physics : CT-02

(Solid State Electronic Devices & Circuits)

(New Course)

Time : $2\frac{1}{2}$ Hours]

[Total Marks : 70

- Instructions :** (1) All questions carry equal marks.
(2) Attempt any five questions out of 10 questions.

1 Answer the following : **14**

- (a) Calculate transconductance (g_m) of JFET having the parameters :
IDSS = 16 mA, $V_p = -4V$ for drain current $I_D = 4 mA$
- (b) Differentiate : Avalanche and Zener breakdown mechanisms.
- (c) Implement two input OR gate by using all NAND gates.
- (d) Distinguish between direct and indirect band gap materials.
- (e) Define fan out for Transistor transistor logic (TTL).
- (f) Calculate wavelength (λ_g) of light emission for GaAs having band gap energy $E_g = 1.44 eV$.
- (g) Prove that product of all the maxterms of a Boolean function of N-variable is 0.

2 Answer the following : **14**

- (a) What is the relation between photometric unit lumen and radiometric unit watt ?
- (b) What is the operational principle of Solar cell ?
- (c) Obtain complement of the following Boolean function :
$$F(x, y, z) = x \cdot (y' \cdot z' + y \cdot z)$$
- (d) Draw JFET transfer characteristic : drain current versus gate to source voltage and define Pinch-off voltage.

- (e) What is the key difference in the physics of light emitting diode and semiconductor laser ?
- (f) What is the advantage of MOS logic over other logic families?
- (g) Write Boolean expression for two input exclusive OR gate.
- 3** (a) Compare : BJT and JFET. Describe the construction of N-channel JFET and explain its drain-source characteristics. **7**
- (b) Discuss various biasing methods for JFET. **7**
- 4** (a) Draw the circuit of 2-input NAND gate using transistor-transistor (TTL) logic and explain its operation. Explain current sinking and current sourcing in TTL. **7**
- (b) Write a detailed note on MOS logic family. **7**
- 5** (a) A logic circuit having three inputs should produce high output for its input binary numbers : 011, 101, 110 and 111. Design the logic circuit using K-Map and draw the circuit using gates. **7**
- (b) Simplify the following Boolean function using Karnaugh Map method : **7**
- $$F(w, x, y, z) = \sum(2, 6, 14, 10) \text{ and don't cares are :}$$
- $$d(w, x, y, z) = \sum(0, 4, 9).$$
- 6** (a) Draw basic structure and symbol of Silicon Controlled Rectifier. Explain the current voltage characteristics of SCR and derive anode current expression for forward blocking state. **7**
- (b) Write a note on characteristic and application of TRIAC. **7**

- 7 (a) Discuss in detail the physics of photoconductive detectors hence derive expression for photoconductive gain. What are the photoconductive materials? 7
- (b) Write detailed note on photo diode and PIN photo diode. 7
- 8 (a) What is a thermistor ? Discuss its characteristic and application 7
- (b) Discuss briefly V-I characteristic of zener diode. Draw the circuit of Zener diode voltage regulator and explain its operation. 7
- 9 (a) Explain working of UJT relaxation oscillator with neat diagrams and derive formula for output frequency. 7
- (b) Write a note on transmissive field effect and reflective type liquid crystal displays. 7
- 10 (a) Explain the physics of light emission in LED. Explain in detail radiative recombination processes. Give a brief note on LED structure and LED materials. 7
- (b) Write a detailed note on semiconductor laser. 7
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